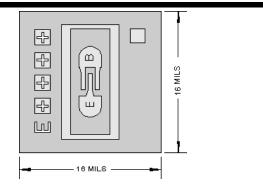


Chip Type 2C918 Geometry 0013 Polarity NPN Data Sheet No. 2C918

## **Generic Packaged Parts:**

**Request Quotation** 

2N918



Chip type **2C918** by Semicoa Semiconductors provides performance similar to these devices.

## Part Numbers:

2N918, 2N918UB, SD918, SD918F, SQ918, SQ918F

## **Product Summary:**

**APPLICATIONS:** Designed for high frequency oscillator, multiplier and driver applications.

## Features:

• High frequency rating

Mechanical Specifications					
Metallization	Тор	AI - 15 kÅ min.			
	Backside	Au - 6.5 kÅ nom.			
Bonding Pad Size	Emitter	2.7 mils x 2.7 mils			
	Base	2.7 mils x 2.7 mils			
Die Thickness	8 mils nominal				
Chip Area	16 mils x 16 mils				
Top Surface	Silox Passivated				

Electrical Characteristics $T_A = 25^{\circ}C$						
Parameter	Test conditions	Min	Max	Unit		
BV <sub>CEO</sub>	$I_{\rm C} = 3.0 \text{ mA}, I_{\rm B} = 0$	15		V dc		
BV <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu A, \ I_{\rm E} = 0$	30		V dc		
BV <sub>EBO</sub>	$I_{\rm E} = 10 \ \mu A, \ I_{\rm C} = 0$	3.0		V dc		
I <sub>CBO</sub>	$V_{CB} = 15 \text{ V}, \text{ I}_{E} = 0$		10	nA		
h <sub>FE</sub>	$I_{\rm C} = 3.0 \text{ mA dc}, V_{\rm CE} = 1.0 \text{ V}$	20				
V <sub>CE(sat)</sub>	$I_{\rm C} = 30 \text{ mA dc}, I_{\rm B} = 3.0 \text{ mA}$		0.3	V dc		

Due to limitations of probe testing, only dc parameters are tested. This must be done with pulse width less than 300  $\mu$ s, duty cycle less than 2%.